

isc Silicon PNP Power Transistor

2SA1700

DESCRIPTION

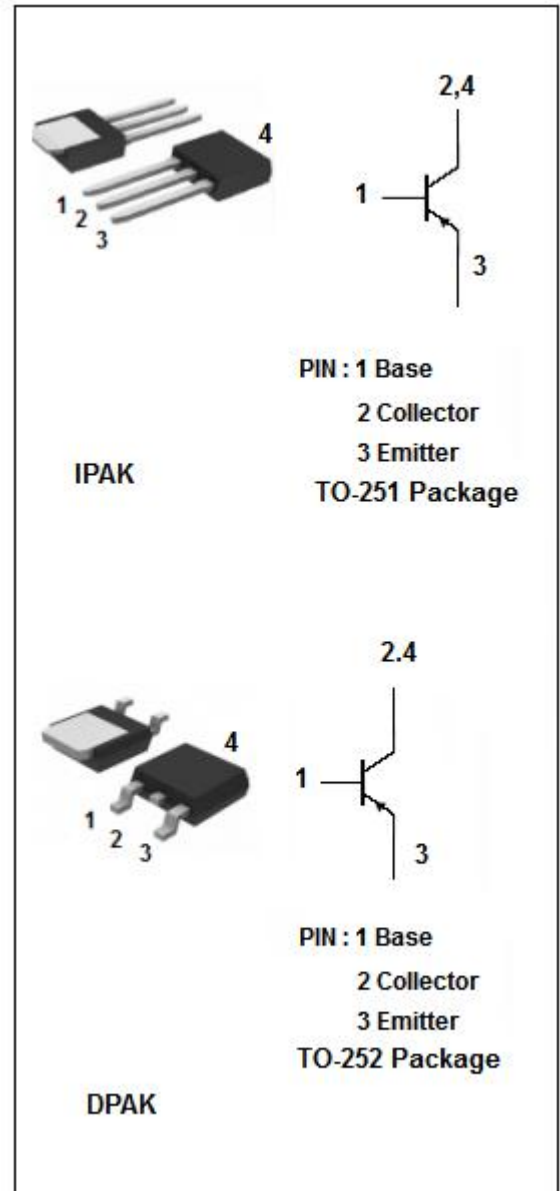
- High breakdown voltage
- Low Collector-Emitter Saturation Voltage
- High Power Dissipation-
: $P_C = 10W @ T_C = 25^\circ C, P_C = 10W @ T_a = 25^\circ C$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- For high voltage driver applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-400	V
V_{CEO}	Collector-Emitter Voltage	-400	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-0.2	A
I_{CM}	Collector Current-Peak	-0.4	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ C$	10	W
	Collector Power Dissipation @ $T_a = 25^\circ C$	1.0	
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



isc Silicon PNP Power Transistor**2SA1700****ELECTRICAL CHARACTERISTICS** $T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -50\text{mA}; I_B = -5\text{mA}$			-0.8	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -50\text{mA}; I_B = -5\text{mA}$			1.0	V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -1\text{mA}; I_B = 0$	-400			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -10\mu\text{A}; I_C = 0$	-5			V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -300\text{V}; I_E = 0$			-0.1	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -4\text{V}; I_C = 0$			-0.1	μA
h_{FE}	DC Current Gain	$I_C = -50\text{mA}; V_{CE} = -10\text{V}$	60		200	
f_T	Current-Gain—Bandwidth Product	$I_C = -10\text{mA}; V_{CE} = -30\text{V}$		70		MHz

◆ **h_{FE} Classifications**

D	E
60-120	100-200

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Outline Drawing

